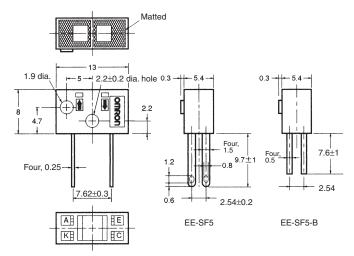
MRON

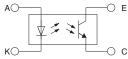
Photomicrosensor (Reflective)

Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Terminal No.

A

Κ

С

Е

Unless otherwise specified, the tolerances are as shown below.

	Dimensions	Tolerance	
	3 mm max.	±0.3	
Name	3 < mm ≤ 6	±0.375	
Anode	6 < mm < 10	±0.45	
Cathode			
Collector	10 < mm ≤ 18	±0.55	
Emitter	$18 < mm \leq 30$	±0.65	

Features

- Dust-tight construction.
- · With a visible-light intercepting filter which allows objects to be sensed without being greatly influenced by the light radiated from fluorescent lamps.
- Mounted with M2 screws.
- · Model with soldering terminals (EE-SF5).
- Model with PCB terminals (EE-SF5-B).
- Recommended sensing distance = 5.0 mm

■ Absolute Maximum Ratings (Ta = 25°C)

	Item	Symbol	Rated value
Emitter	Forward current	I _F	50 mA (see note 1)
	Pulse forward cur- rent	I _{FP}	1 A (see note 2)
	Reverse voltage	V _R	4 V
Detector	Collector–Emitter voltage	V _{CEO}	30 V
	Emitter–Collector voltage	V _{ECO}	
	Collector current	I _C	20 mA
	Collector dissipa- tion	P _c	100 mW (see note 1)
Ambient tem-	Operating	Topr	–25°C to 80°C
perature	Storage	Tstg	–30°C to 80°C
Soldering temperature		Tsol	260°C (see note 3)

Note: 1. Refer to the temperature rating chart if the ambient temperature exceeds 25°C.

- 2. The pulse width is 10 μs maximum with a frequency of 100 Hz.
- 3. Complete soldering within 10 seconds.

■ Electrical and Optical Characteristics (Ta = 25°C)

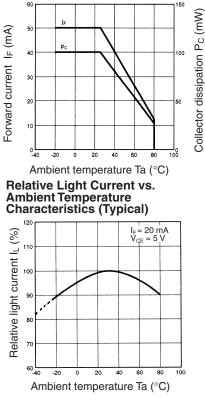
Item		Symbol	Value	Condition
Emitter	Forward voltage	V _F	1.2 V typ., 1.5 V max.	I _F = 30 mA
	Reverse current	I _R	0.01 μA typ., 10 μA max.	$V_{R} = 4 V$
	Peak emission wavelength	λ _P	940 nm typ.	I _F = 20 mA
Detector	Light current	IL.	200 μA min., 2,000 μA max.	$I_F = 20$ mA, $V_{CE} = 10$ V White paper with a reflection ratio of 90%, d = 5 mm (see note)
	Dark current	I _D	2 nA typ., 200 nA max.	V _{CE} = 10 V, 0 <i>l</i> x
	Leakage current	I _{LEAK}	2 μA max.	$I_F = 20 \text{ mA}, V_{CE} = 10 \text{ V}$ with no reflection
	Collector–Emitter saturated volt- age	V _{CE} (sat)		
	Peak spectral sensitivity wave- length	λ_{P}	850 nm typ.	V _{CE} = 10 V
Rising time		tr	30 μs typ.	$V_{CC} = 5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega, \text{ I}_{L} = 1 \text{ mA}$
Falling time		tf	30 μs typ.	$V_{CC} = 5 \text{ V}, \text{ R}_{L} = 1 \text{ k}\Omega, \text{ I}_{L} = 1 \text{ mA}$

Note: The letter "d" indicates the distance between the top surface of the sensor and the sensing object.

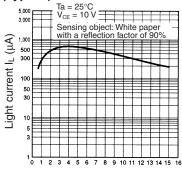
OMRON

Engineering Data

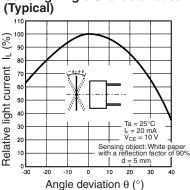
Forward Current vs. Collector Dissipation Temperature Rating



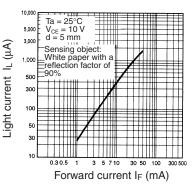
Sensing Distance Characteristics (Typical)



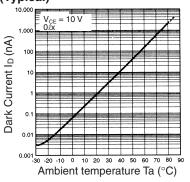
Distance d (mm) Sensing Angle Characteristics (Typical)



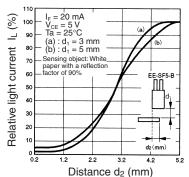
Light Current vs. Forward Current Characteristics (Typical)



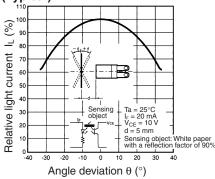
Dark Current vs. Ambient Temperature Characteristics (Typical)



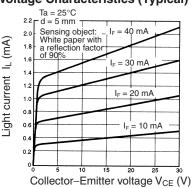
Sensing Position Characteristics (Typical)



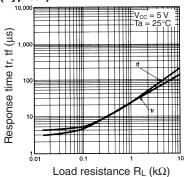




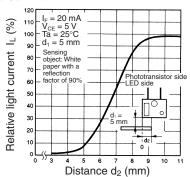
Light Current vs. Collector–Emitter Voltage Characteristics (Typical)



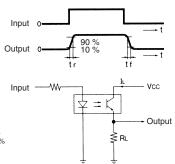
Response Time vs. Load Resistance Characteristics (Typical)



Sensing Position Characteristics (Typical)



Response Time Measurement Circuit



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